# N-Channel 20-V (D-S) MOSFET

## CHARACTERISTICS

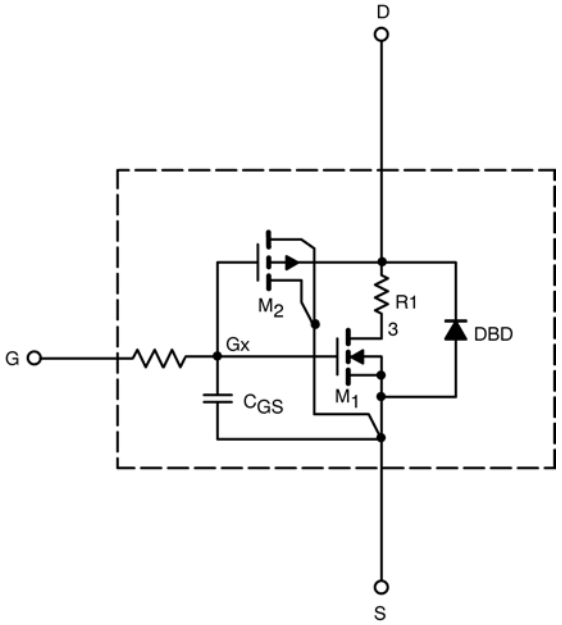
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the −55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

## DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the −55 to 125°C temperature ranges under the pulsed 0-V to 10-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

## SUBCIRCUIT MODEL SCHEMATIC

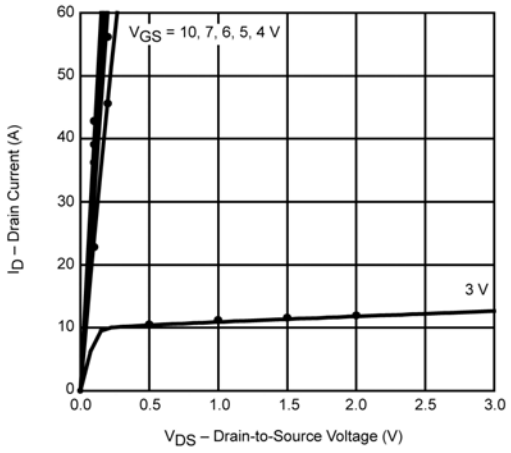


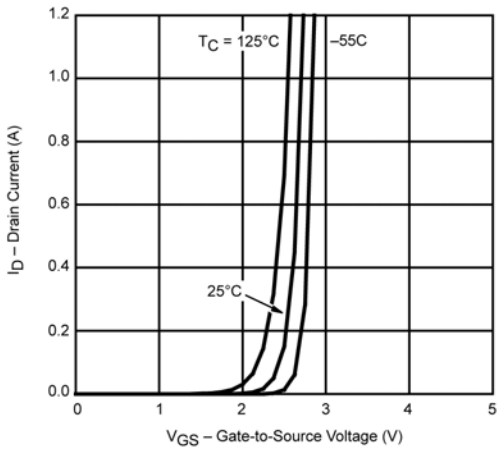

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

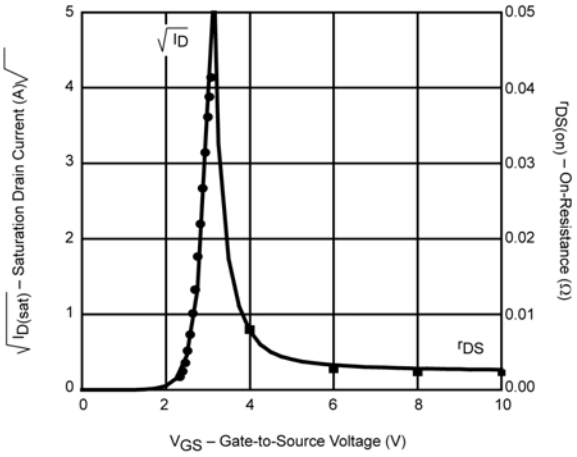
| SPECIFICATIONS ($T_J$ = 25°C UNLESS OTHERWISE NOTED) | | | | | |
|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Condition** | **Simulated Data** | **Measured Data** | **Unit** |
| **Static** | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 μA | 1.8 | | V |
| On-State Drain Current[a] | $I_{D(on)}$ | $V_{DS}$ ≥ 5 V, $V_{GS}$ = 10 V | 1671 | | A |
| Drain-Source On-State Resistance[a] | $r_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 20 A | 0.0026 | 0.0026 | Ω |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 17 A | 0.0036 | 0.0036 | |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = 15 V, $I_D$ = 20 A | 23 | 92 | S |
| Diode Forward Voltage[a] | $V_{SD}$ | $I_S$ = 2.7 A | 0.76 | 0.72 | V |
| **Dynamic[b]** | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$ = 10 V, $V_{GS}$ = 0 V, f = 1 MHz | 3355 | 3380 | pF |
| Output Capacitance | $C_{oss}$ | | 807 | 797 | |
| Reverse Transfer Capacitance | $C_{rss}$ | | 282 | 335 | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = 10 V, $V_{GS}$ = 10 V, $I_D$ = 10 A | 50 | 51.5 | nC |
| | | $V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_D$ = 10 A | 24.5 | 24.5 | |
| Gate-Source Charge | $Q_{gs}$ | | 10.3 | 10.3 | |
| Gate-Drain Charge | $Q_{gd}$ | | 6.5 | 6.5 | |

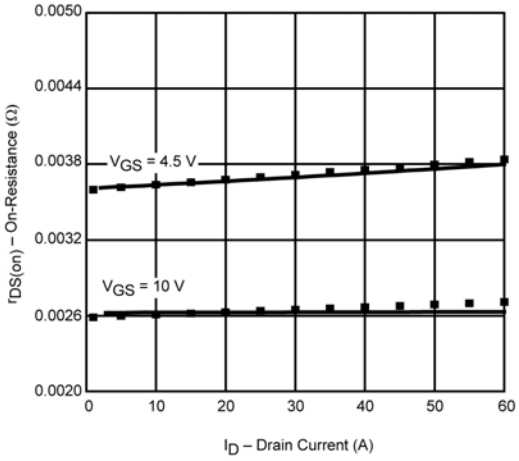
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

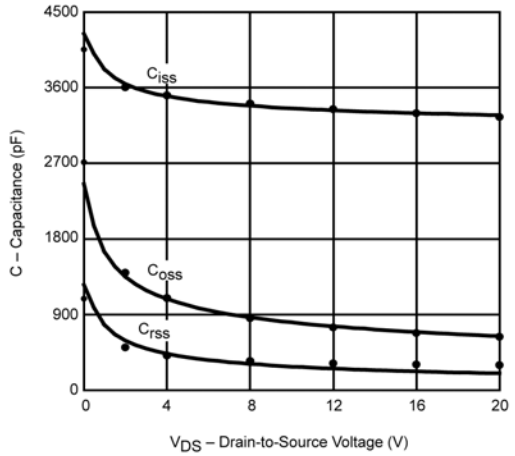
COMPARISON OF MODEL WITH MEASURED DATA ($T_J$=25°C UNLESS OTHERWISE NOTED)

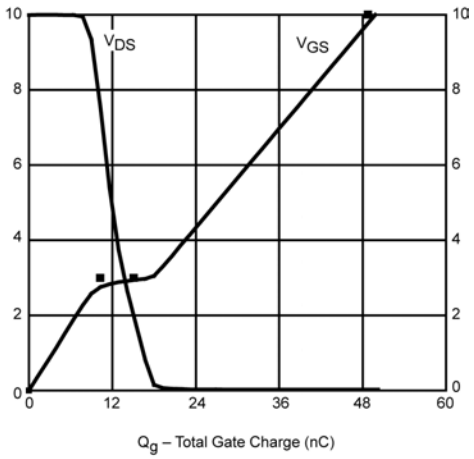



Note: Dots and squares represent measured data.